

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

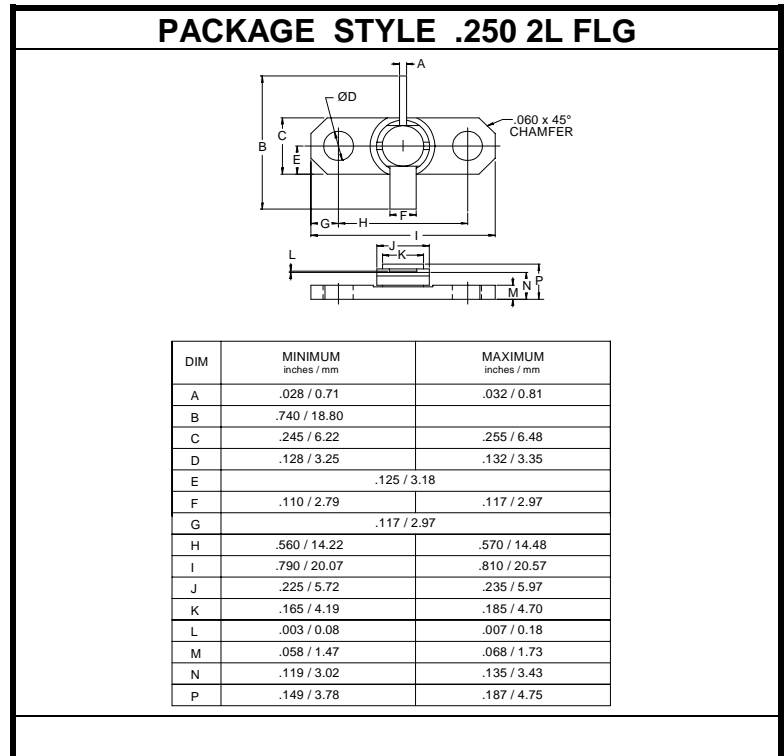
The **ASI NEX230165** is Designed for General Purpose Power oscillator Amplifier Applications up to 2.3 GHz.

**FEATURES:**

- Common Collector
- Hermetic Microstrip Package
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	600 mA
<b>V<sub>CEO</sub></b>	20 V
<b>V<sub>CBO</sub></b>	45 V
<b>V<sub>EBO</sub></b>	3.0 V
<b>P<sub>DISS</sub></b>	7.0 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	25 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 30 V			.25	<b>mA</b>
<b>I<sub>EBO</sub></b>	V <sub>EB</sub> = 2.0 V			.25	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 100 mA	15		120	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 20 V      f = 1.0 MHz		1.5	2.5	<b>pF</b>
<b>P<sub>osc</sub></b>	V <sub>CE</sub> = 18 V      I <sub>E</sub> = 250 mA      f = 2.3 GHz		1.6		<b>W</b>